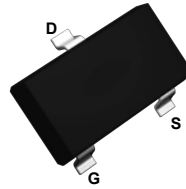
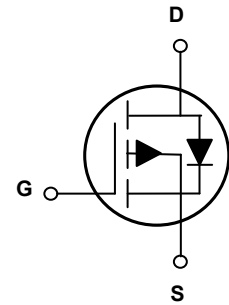


Main Product Characteristics

$V_{(BR)DSS}$	-60V
$R_{DS(ON)}$	190mΩ
I_D	-2A



SOT-23



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for motor drive, power tools and LED lighting
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The SSF6911S utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current – Continuous (T _C =25°C)	I _D	-2	A
Drain Current – Continuous (T _C =100°C)		-1.25	A
Drain Current – Pulsed ¹	I _{DM}	-8	A
Power Dissipation (T _C =25°C)	P _D	1.56	W
Power Dissipation – Derate above 25°C	P _D	0.012	W/°C
Storage Temperature Range	T _{STG}	-50 to +150	°C
Operating Junction Temperature Range	T _J	-50 to +150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction to Ambient	R _{θJA}	---	80	°C/W


Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.05	---	$V/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-48V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	-10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	μA
On Characteristics						
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-2A$	---	160	190	$m\Omega$
		$V_{GS}=-4.5V, I_D=-1.5A$	---	200	240	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.9	-2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	5	---	$mV/^\circ\text{C}$
Forward Transconductance	g_{fs}	$V_{DS}=-10V, I_S=-2A$	---	3.5	---	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{2, 3}	Q_g	$V_{DS}=-30V, V_{GS}=-10V, I_D=-2A$	---	8.2	12	nC
Gate-Source Charge ^{2, 3}	Q_{gs}		---	1.8	3.6	
Gate-Drain Charge ^{2, 3}	Q_{gd}		---	1.5	3	
Turn-On Delay Time ^{2, 3}	$T_{d(on)}$	$V_{DD}=-30V, V_{GS}=-10V, R_G=6\Omega, I_D=-1A$	---	5.2	10	nS
Rise Time ^{2, 3}	T_r		---	19	36	
Turn-Off Delay Time ^{2, 3}	$T_{d(off)}$		---	35	67	
Fall Time ^{2, 3}	T_f		---	10.6	20	
Input Capacitance	C_{iss}	$V_{DS}=-30V, V_{GS}=0V, F=1\text{MHz}$	---	425	615	pF
Output Capacitance	C_{oss}		---	35	50	
Reverse Transfer Capacitance	C_{rss}		---	20	30	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V$, Force Current	---	---	-2	A
Pulsed Source Current	I_{SM}		---	---	-4	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V

Notes:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

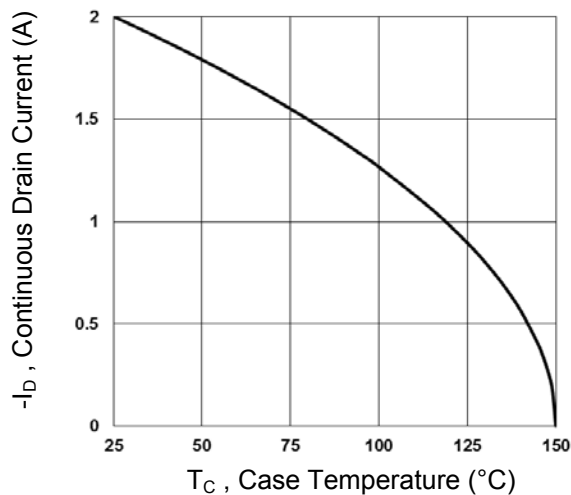


Fig.1 Continuous Drain Current vs. T_c

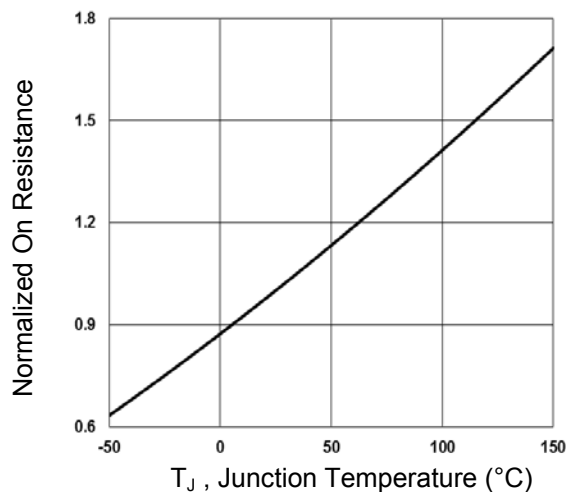


Fig.2 Normalized $R_{DS(ON)}$ vs. T_j

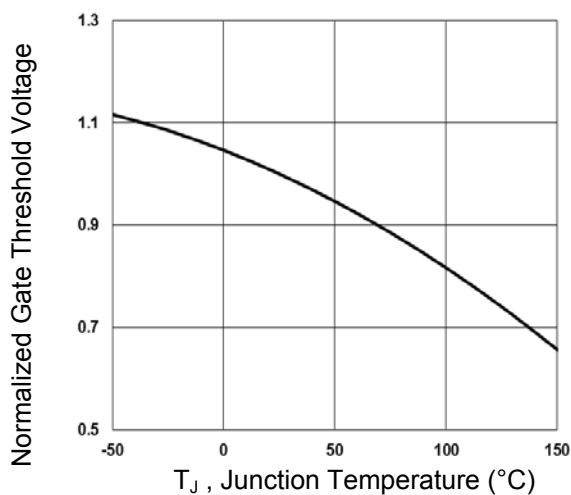


Fig.3 Normalized V_{th} vs. T_j

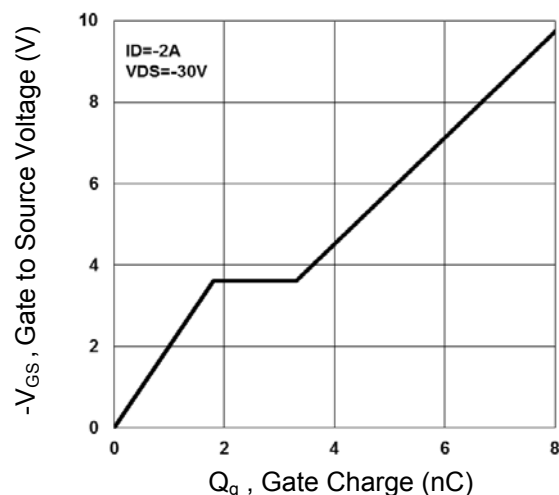


Fig.4 Gate Charge Waveform

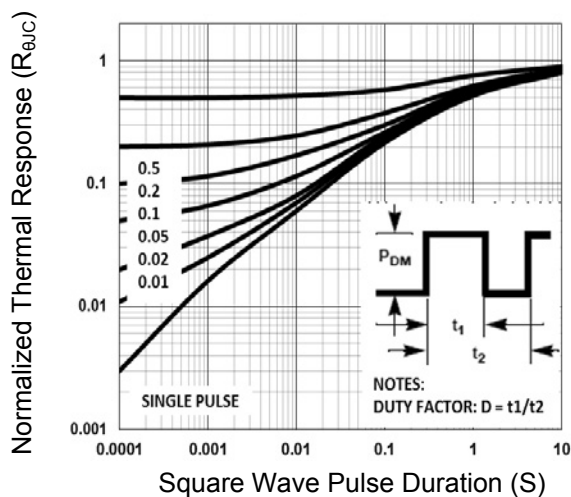


Fig.5 Normalized Transient Impedance

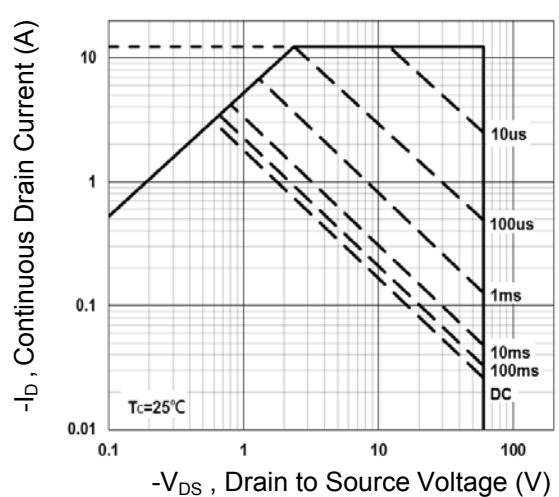


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

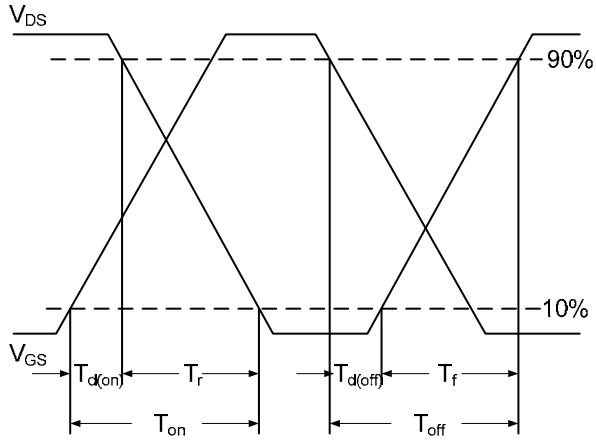


Fig.7 Switching Time Waveform

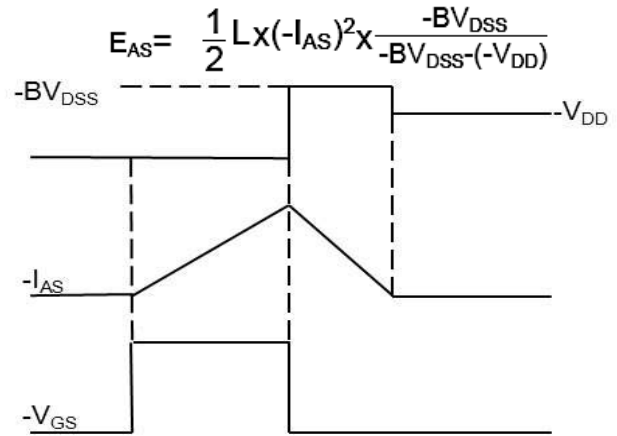
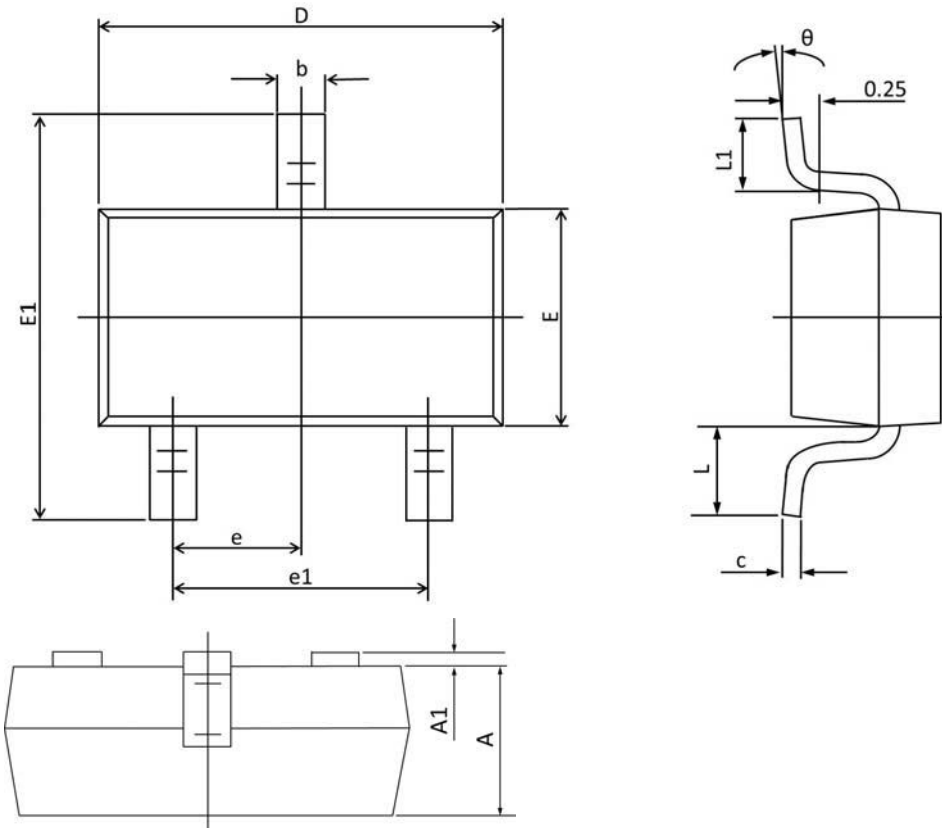


Fig.8 E_{AS} Waveform

Package Outline Dimensions

SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.000	0.035	0.039
A1	0.000	0.100	0.000	0.004
b	0.300	0.500	0.012	0.020
c	0.090	0.110	0.003	0.004
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	1°	7°	1°	7°